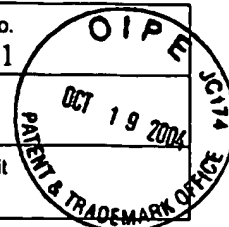


Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-051002	Application No. 10/727,651
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Shunpei Yamazaki, et al.	
		Filing Date December 5, 2003	Group Art Unit 2811



U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
AS	AA	2003/0102480	06/05/2003	YAMAZAKI et al.			11/18/2002
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
AS	AL	DE 19825081	10DEC 1998	GERMANY			Abstract	
AS	AM	DE19833237	28 JAN 1999	GERMANY			Abstract	
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
AS	AQ	Partial European Search Report (Application No. 01114265.0), August 13, 2004, 4 pages.
	AR	
	AS	
	AT	

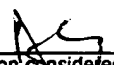
Examiner Signature AS	Date Considered 4/14/05
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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Sheet 1 of 2

Substitute Form PTO-1449 (Modified) Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-051002	Application No. New Application
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	Filing Date December 5, 2003	Group Art Unit Unknown	

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
X.S.	AA	4,766,477	08/23/1988	Nakagawa, et al.			
	AB	5,643,826	07/01/1997	Ohtani, et al.			
	AC	5,923,962	07/13/1999	Ohtani, et al.			
	AD	5,943,560	08/24/1999	Chang, et al.			
	AE	5,977,560	11/02/1999	Banerjee, et al.			
	AF	6,087,679	07/2000	Yamazaki, et al.			
	AG	US 2002/0043662	04/18/2002	Yamazaki, et al.			
	AH	US 2002/0038889	04/04/2002	Yamazaki, et al.			
	AI	US 2002/0014625	02/07/2002	Asami, et al.			
	AJ	US 2002/0008286	01/24/2002	Yamazaki, et al.			
	AK	US 2002/0040981	04/2002	Yamazaki, et al.			
	AL	US 2003/0001159	01/02/2003	Ohtani, et al.			
	AM	5,162,933	11/10/1992	Kakuda, et al.			
	AN	5,304,407	04/19/1994	Hayashi, et al.			
	AO	5,602,424	02/1997	Tsubouchi, et al.			
	AP	5,686,980	11/11/1997	Hirayama, et al.			
	AQ	5,932,893	08/03/1999	Miyanaga, et al.			
	AR	6,107,639	08/22/2000	Yamazaki, et al.			
	AS	6,107,654	08/22/2000	Yamazaki, et al.			
	AT	6,180,957	01/30/2001	Miyasaka, et al.			
	AU	6,285,042	09/04/2001	Ohtani, et al.			
	AV	6,307,214	10/23/2001	Ohtani, et al.			
	AW	6,307,220	10/23/2001	Yamazaki			
	AX	6,335,541	01/01/2002	Ohtani, et al.			
	AY	6,348,368	02/19/2002	Yamazaki, et al.			
V	AZ	6,452,211	09/17/2002	Ohtani, et al.			

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	BA	6,495,886	12/17/2002	Yamazaki, et al.			06/13/2002
	BB						

Foreign Patent Documents or Published Foreign Patent Applications								
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
<u>A-S</u>	BC	8-78329	03/22/1996	Japan			Abstract	
	BD	7-130652	05/19/1995	Japan			Abstract	
	BE	TW 251379	07/11/1995	Taiwan			Full	
	BF	TW 310478	07/11/1997	Taiwan			Full	
	BG	JP 11-345767	12/1999	Japan				
	BH	JP 4-349619	12/1992	Japan				
	BI	EP 984317	03/2000	Europe				
	BJ	02-219234	08/31/1990	Japan			Abstract	
	BK	11-204434	07/30/1999	Japan			Abstract	
	BL	11-284198	10/15/1999	Japan			Abstract	
	BM	11-307783	11/05/1999	Japan			Abstract	
	BN	EP 510969	04/1991	Europe				
<u>Y</u>	BO							

Other Documents (include Author, Title, Date, and Place of Publication)		
Examiner Initial	Desig. ID	Document
<u>X</u>	BP	R. Ishihara et al.; "Micro Texture Analysis Of Location Controlled Large Si Grain Formed by Excimer-Laser Crystallization Method"; <i>AMLCD '99 Digest of Technical Papers 1999 Tokyo, Japan</i> ; pp. 99-102; 1999
<u>X</u>	BQ	Seok-Woon Lee et al.; "Low Temperature Poly-Si Thin-Film Transistor Fabrication by Metal-Induced Lateral Crystallization"; <i>IEEE Electron Device Letters</i> , Vol. 17, No. 4, pp. 160-162; April 1996
	BR	

Examiner Signature <u>Ac</u>	Date Considered <u>4/14/05</u>
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(37 CFR §1.98(b))			

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	AP	5,686,980	11/11/1997	Hirayama, et al.			
	AQ	5,932,893	08/03/1999	Miyanaga, et al.			
	AR	6,107,639	08/22/2000	Yamazaki, et al.			
	AS	6,107,654	08/22/2000	Yamazaki, et al.			
	AT	6,180,957	01/30/2001	Miyasaka, et al.			
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	AW	6,307,220	10/23/2001	Yamazaki			
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	BH	JP 4-349619	12/1992	Japan			Abstract	
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	BK	11-204434	07/30/1999	Japan			Abstract	
	BL	11-284198	10/15/1999	Japan			Abstract	
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X	BQ	Seok-Woon Lee et al.; "Low Temperature Poly-Si Thin-Film Transistor Fabrication by Metal-Induced Lateral Crystallization"; <i>IEEE Electron Device Letters</i> , Vol. 17, No. 4, pp. 160-162; April 1996
	BR	

X Did not receive

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